LJ13003-74

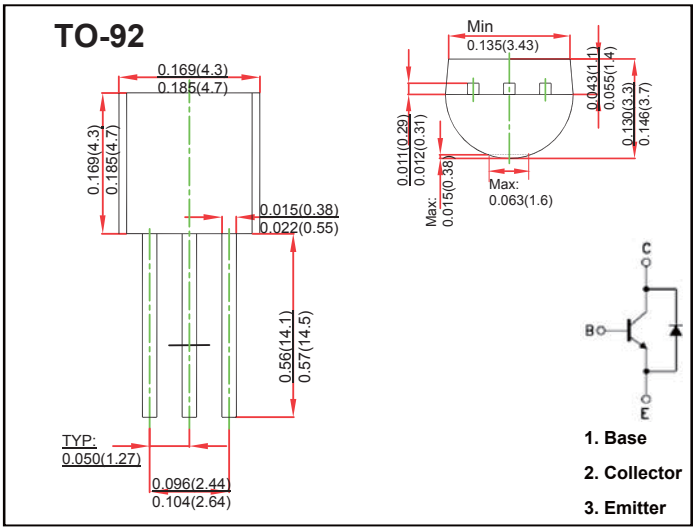
TO-92 Plastic-Encapsulate Transistors

FEATURES

- NPN Transistors
- Low switching loss and high reliability
- High temperature characteristics
- Reverse leakage

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS

(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	600	V
V_{CEO}	Collector Emitter Voltage	400	V
V_{EBO}	Emitter Base Voltage	9	V
I_C	Collector Current	1	A
P_{tot}	Total Power Dissipation	1.25	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C = 0.1mA, I_E = 0	600			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = 1mA, I_B = 0	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E = 0.1mA, I_C = 0	9			V
I_{CBO}	Collector cut-off current	V_{CB} = 600V, I_E = 0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB} = 9V, I_C = 0			10	μA
h_{FE}	DC current gain	V_{CE} = 5V, I_C = 200mA	15		30	
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C = 500mA,I_B = 100mA			0.5	V
V_{ECF}		I_C = 1.5A			2.5	V
t_s	Storage time	UI9600A, I_C = 0.25A	1.5		4.0	μs
f_T	Transition frequency	V_{CE} = 10V, I_C = 0.1A, f = 1MHZ	5			MHz

RATINGS AND CHARACTERISTIC CURVES

Typical Characterisitics